Features

- Super Low Gate Charge
- Green Device Available
- Excellent CdvV/dt effect decline
- Advanced high cell density Trench technology
- 100% EAS Guaranteed

Bvdss	Rdson	ID
-60V	46mΩ	-20A

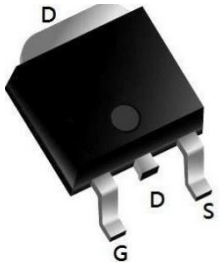
Application

RoHS

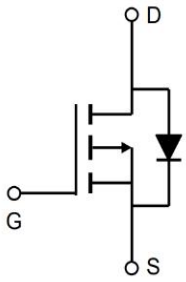
- PWM applications
- Load Switch
- Power management

Package

Marking and pin assignment



TO252-3L top view



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Quantity
20P06	20P06	TO252-3L	2500

Absolute Maximum Ratings (T_A=25℃unless otherwise specified noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current,V_{GS}@-10V[1]	I_D@T_C=25℃	-20	A
	I_D@T_C=100℃	-12	A
Pulsed Drain Current[2]	I_{DM}	-30	A
Single Pulse Avalanche Energy[3]	EAS	18.5	mJ
Avalanche Current	I_{AS}	-13.1	A
Total Power Dissipation[4]	P_D	2	W
Storage Temperature Range	T_{STG}	-55 ~ 150	℃
Operating Junction Temperature Range	T_J	-55 ~ 150	℃

Thermal Resistance Ratings

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance from Junction to Ambient[1]	$R_{\theta JA}$	--	63	℃/W
Thermal Resistance from Junction to Case[1]	$R_{\theta JC}$	--	5	℃/W

Ordering Information

Ordering Number	Package	Pin Assignment			Packing
Halogen Free		G	D	S	
HL20P06	TO252-3L	1	2	3	Tape Reel

Electrical Characteristics (T_J=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=-250μA	-60	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-1	uA
Gate-body Leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.2	-1.7	-2.5	V
Drain-Source On-Resistance[2]	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-10A	-	47	57	mΩ
		V_{GS}=-4.5V, I_D=-6A	-	55	66	mΩ
Forward Transconductance	gfs	V_{DS}=-5V,I_D=-15A	-	12	-	S
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V, f=1MHz	-	580	-	pF
Output Capacitance	C_{oss}		-	98	-	
Reverse Transfer Capacitance	C_{rss}		-	84	-	
Total Gate Charge	Q_g	V_{GS}=-4.5V,I_D=-15A, V_{DS}=-15V	-	6	-	nC
Gate-Source Charge	Q_{gs}		-	3	-	
Gate-Drain Charge	Q_{gd}		-	1.75	-	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V,R_G=3.3Ω, I_D=-15A,V_{GS}=-10V	-	2.5	-	nS
Rise Time	t_r		-	8.5	-	
Turn-Off Delay Time	$t_{d(off)}$		-	33.5	-	
Fall Time	t_f		-	6	-	
Continuous Source Current[1,5]	I_S	V_G=V_D=0V,Force Current	-	-	-20	A
Pulsed Source Current[2,5]	I_{SM}		-	-	-30	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V,I_S=-15A	-	-	-1.2	V
Reverse Recovery Time	trr	I_F=-15A,dI/dt=-100A/us	-	6	-	nC
Reverse Recovery Charge	Qrr		-	1.5	-	

Notes:

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-19A

4.The power dissipation is limited by 150℃ junction temperature.

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

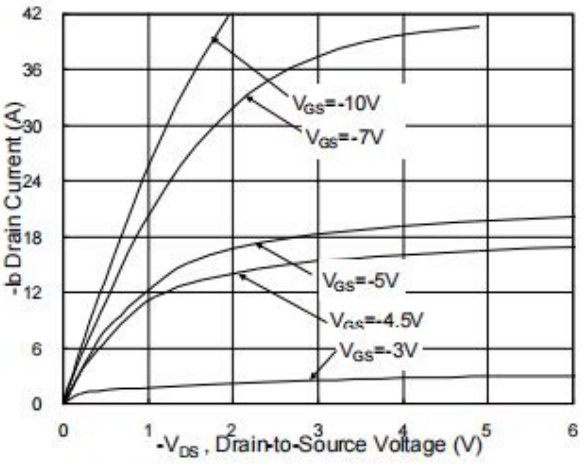


Fig.1 Typical Output Characteristics

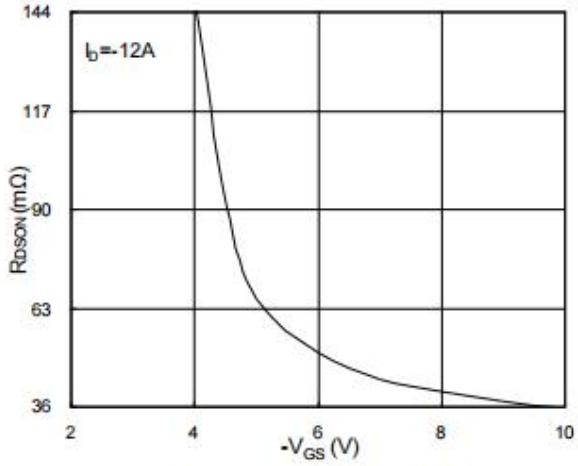


Fig.2 On-Resistance v.s Gate-Source

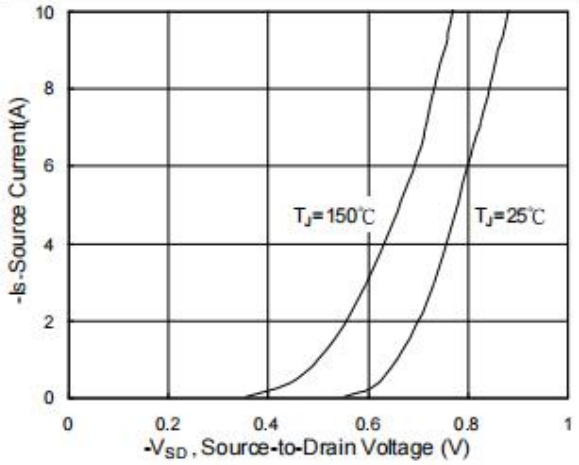


Fig.3 Forward Characteristics Of Reverse

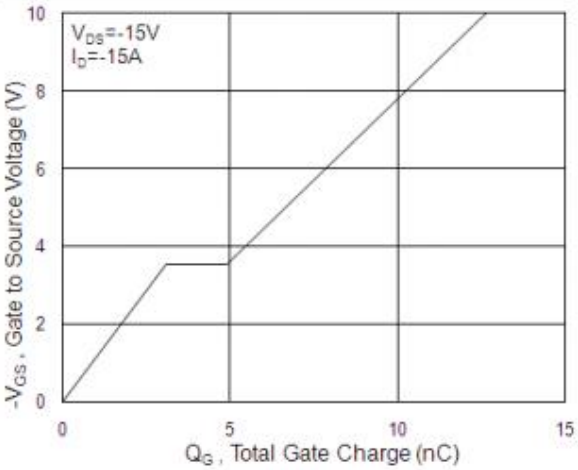


Fig.4 Gate Charge Characteristics

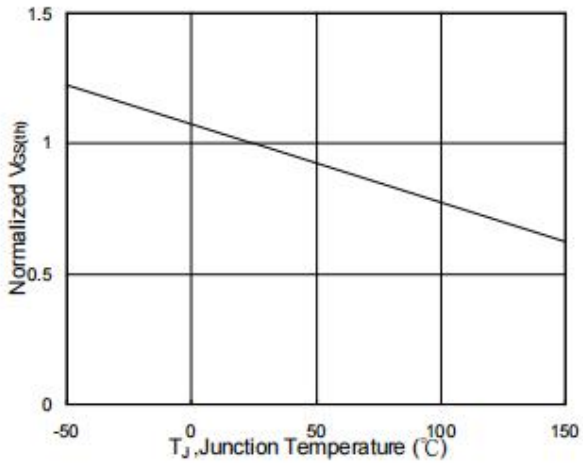


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

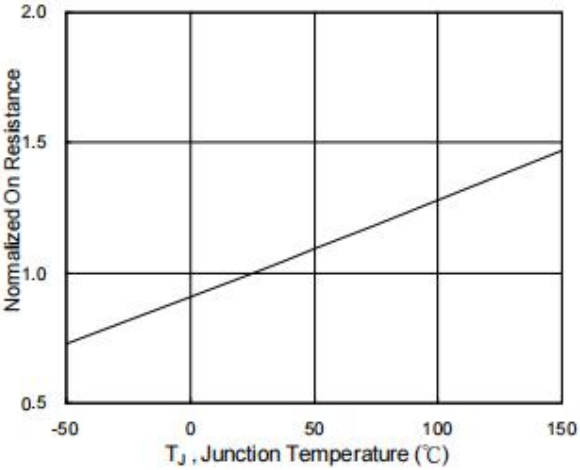


Fig.6 Normalized R_{DSON} vs. T_J

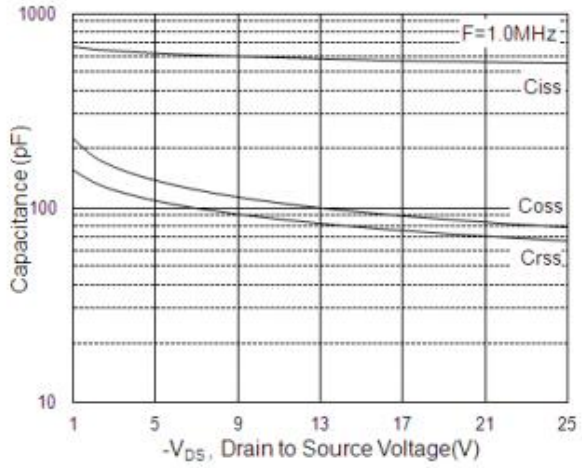


Fig.7 Capacitance

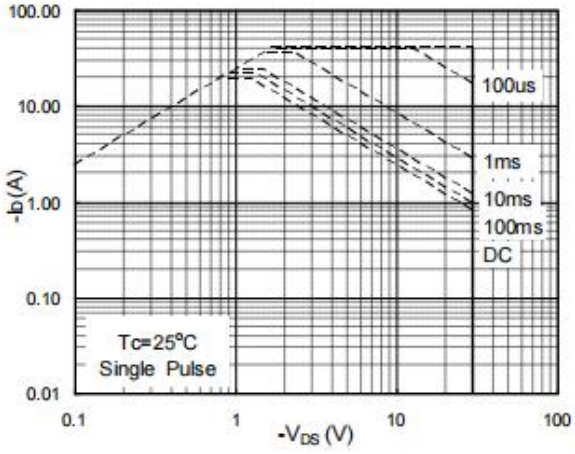


Fig.8 Safe Operating Area

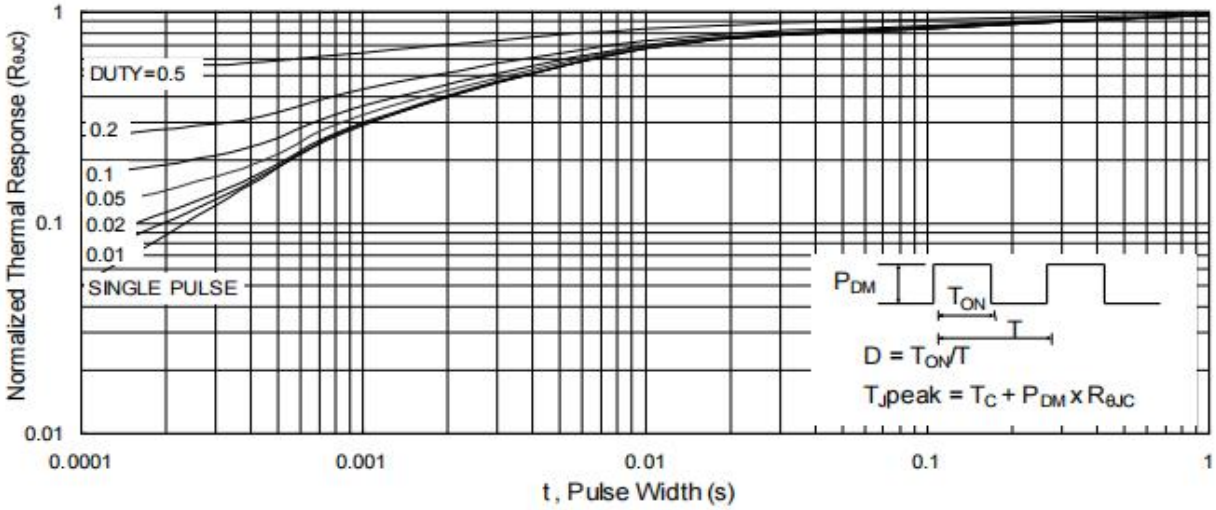


Fig.9 Normalized Maximum Transient Thermal Impedance

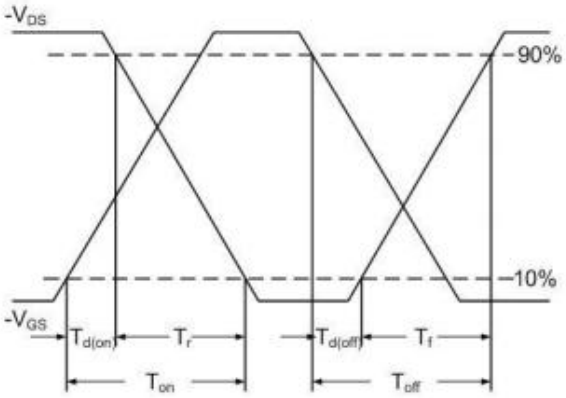


Fig.10 Switching Time Waveform

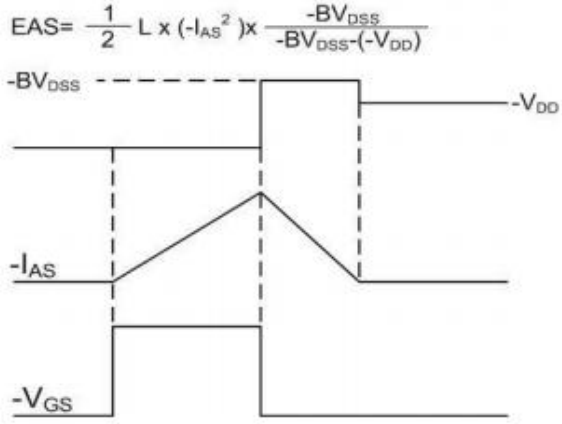
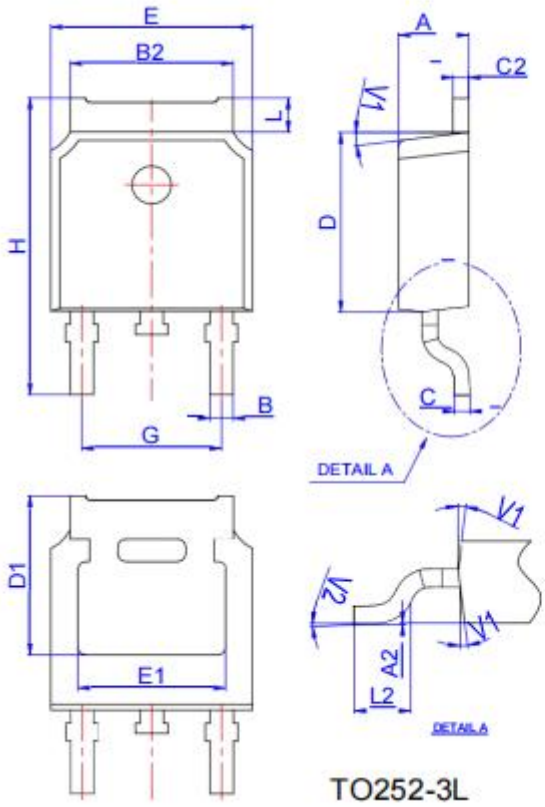


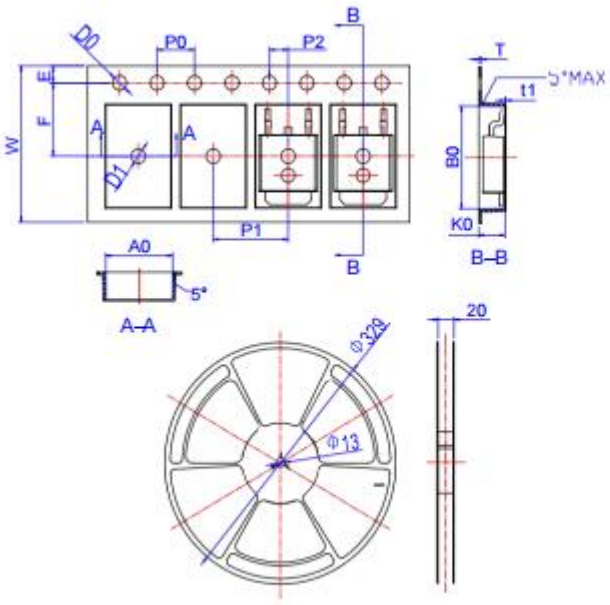
Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data TO252-3L



TO252-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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